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Kind regards,

Team Nexperia

# HEF40106B-Q100

# Hex inverting Schmitt trigger Rev. 1 — 7 August 2012

**Product data sheet** 

#### **General description** 1.

The HEF40106B-Q100 provides six inverting buffers. Each input has a Schmitt trigger circuit. The inverting buffer switches at different points for positive-going and negative-going signals. The difference between the positive voltage (V<sub>T+</sub>) and the negative voltage (V<sub>T</sub>) is defined as hysteresis voltage (V<sub>H</sub>).

The HEF40106B-Q100 may be used for enhanced noise immunity or to "square up" slowly changing waveforms.

It operates over a recommended V<sub>DD</sub> power supply range of 3 V to 15 V referenced to V<sub>SS</sub> (usually ground). Unused inputs must be connected to V<sub>DD</sub>, V<sub>SS</sub>, or another input.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

#### 2. **Features and benefits**

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - ◆ Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Schmitt trigger input discrimination
- Fully static operation
- 5 V, 10 V, and 15 V parametric ratings
- Standardized symmetrical output characteristics
- ESD protection:
  - ◆ MIL-STD-833, method 3015 exceeds 2000 V
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Complies with JEDEC standard JESD 13-B

# **Applications**

- Wave and pulse shapers
- Astable multivibrators
- Monostable multivibrators



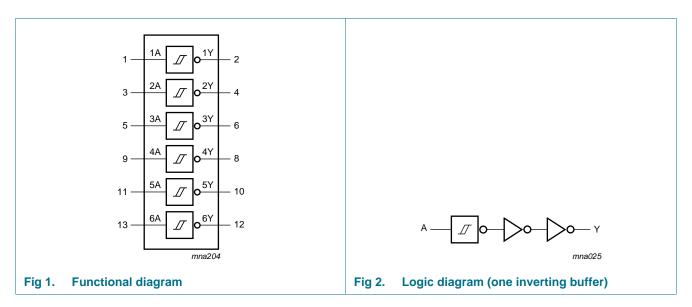
## 4. Ordering information

#### Table 1. Ordering information

All types operate from -40 °C to +125 °C

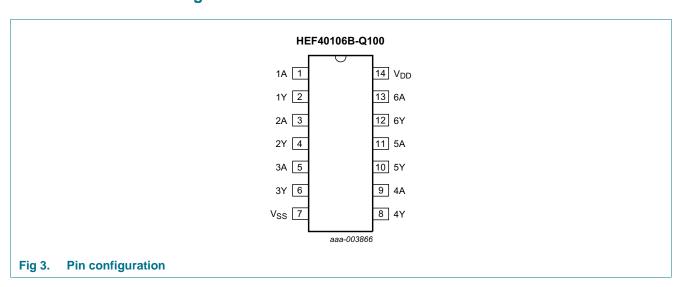
Type number	Package								
	Name	Description	Version						
HEF40106BT-Q100	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1						
HEF40106BTT-Q100	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1						

# 5. Functional diagram



# 6. Pinning information

#### 6.1 Pinning



HEF40106B\_Q100

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#### 6.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1A to 6A	1, 3, 5, 9, 11, 13	input
1Y to 6Y	2, 4, 6, 8, 10, 12	output
$V_{DD}$	14	supply voltage
$V_{SS}$	7	ground (0 V)

# 7. Functional description

Table 3. Function table[1]

Input	Output
nA	nY
L	Н
Н	L

<sup>[1]</sup> H = HIGH voltage level; L = LOW voltage level.

# 8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to  $V_{SS} = 0 \text{ V}$  (ground).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DD}$	supply voltage		-0.5	+18	V
I <sub>IK</sub>	input clamping current	$V_{I} < -0.5 \text{ V or } V_{I} > V_{DD} + 0.5 \text{ V}$	-	±10	mA
VI	input voltage		-0.5	$V_{DD} + 0.5$	V
I <sub>OK</sub>	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{DD} + 0.5 \text{ V}$	-	±10	mA
I <sub>I/O</sub>	input/output current		-	±10	mA
$I_{DD}$	supply current		-	50	mΑ
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>amb</sub>	ambient temperature		-40	+125	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40  ^{\circ}\text{C} \text{ to } +125  ^{\circ}\text{C}$			
		SO14	<u>[1]</u> _	500	mW
		TSSOP14	[2] _	500	mW
Р	power dissipation	per output	-	100	mW

<sup>[1]</sup> For SO14 packages: above  $T_{amb}$  = 70 °C,  $P_{tot}$  derates linearly with 8 mW/K.

<sup>[2]</sup> For TSSOP14 packages: above  $T_{amb}$  = 60 °C,  $P_{tot}$  derates linearly with 5.5 mW/K.

# 9. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DD}$	supply voltage		3	15	V
$V_{I}$	input voltage		0	$V_{DD}$	V
T <sub>amb</sub>	ambient temperature	in free air	-40	+125	°C

#### 10. Static characteristics

Table 6. Static characteristics

 $V_{SS} = 0$  V;  $V_I = V_{SS}$  or  $V_{DD}$ ; unless otherwise specified.

Symbol	Parameter	Conditions	$V_{DD}$	T <sub>amb</sub> =	-40 °C	T <sub>amb</sub> =	+25 °C	T <sub>amb</sub> =	+85 °C	T <sub>amb</sub> =	+125 °C	Unit
				Min	Max	Min	Max	Min	Max	Min	Max	
$V_{OH}$	HIGH-level	$ I_{O}  < 1 \mu A$	5 V	4.95	-	4.95	-	4.95	-	4.95	-	V
	output voltage		10 V	9.95	-	9.95	-	9.95	-	9.95	-	V
			15 V	14.95	-	14.95	-	14.95	-	14.95	-	V
$V_{OL}$	LOW-level	$ I_O  < 1 \mu A$	5 V	-	0.05	-	0.05	-	0.05	-	0.05	V
	output voltage		10 V	-	0.05	-	0.05	-	0.05	-	0.05	V
			15 V	-	0.05	-	0.05	-	0.05	-	0.05	V
I <sub>OH</sub>	HIGH-level	$V_0 = 2.5 \text{ V}$	5 V	-	-1.7	-	-1.4	-	-1.1	-	-1.1	mΑ
	output current	$V_0 = 4.6 \text{ V}$	5 V	-	-0.64	-	-0.5	-	-0.36	-	-0.36	mΑ
		V <sub>O</sub> = 9.5 V	10 V	-	-1.6	-	-1.3	-	-0.9	-	-0.9	mΑ
		V <sub>O</sub> = 13.5 V	15 V	-	-4.2	-	-3.4	-	-2.4	-	-2.4	mΑ
I <sub>OL</sub>	LOW-level	$V_0 = 0.4 \ V$	5 V	0.64	-	0.5	-	0.36	-	0.36	-	mΑ
	output current	V <sub>O</sub> = 0.5 V	10 V	1.6	-	1.3	-	0.9	-	0.9	-	mΑ
		V <sub>O</sub> = 1.5 V	15 V	4.2	-	3.4	-	2.4	-	2.4	-	mΑ
I <sub>I</sub>	input leakage current		15 V	-	±0.1	-	±0.1	-	±1.0	-	±1.0	μΑ
I <sub>DD</sub>	supply current	all valid input	5 V	-	0.25	-	0.25	-	7.5	-	7.5	μΑ
		combinations; $I_0 = 0 A$	10 V	-	0.5	-	0.5	-	15.0	-	15.0	μΑ
			15 V	-	1.0	-	1.0	-	30.0	-	30.0	μΑ
Cı	input capacitance			-	-	-	7.5	-	-	-	-	pF

# 11. Dynamic characteristics

Table 7. Dynamic characteristics

 $T_{amb}$  = 25 °C;  $C_L$  = 50 pF;  $t_r$  =  $t_f$  ≤ 20 ns; wave forms see <u>Figure 4</u>; test circuit see <u>Figure 5</u>; unless otherwise specified.

Symbol	Parameter	Conditions	$V_{DD}$	Extrapolation formula[1]	Min	Тур	Max	Unit
$t_{PHL}$	HIGH to LOW	nA or nB to nY	5 V	63 ns + (0.55 ns/pF)C <sub>L</sub>	-	90	180	ns
	propagation delay		10 V	29 ns + (0.23 ns/pF)C <sub>L</sub>	-	35	70	ns
			15 V	22 ns + (0.16 ns/pF)C <sub>L</sub>	-	30	60	ns
t <sub>PLH</sub>	LOW to HIGH	nA or nB to nY	5 V	58 ns + (0.55 ns/pF)C <sub>L</sub>	-	75	150	ns
propagation delay	propagation delay		10 V	29 ns + (0.23 ns/pF)C <sub>L</sub>	-	35	70	ns
			15 V	22 ns + (0.16 ns/pF)C <sub>L</sub>	-	30	60	ns
$t_{THL}$	HIGH to LOW output transition time	nY to LOW	5 V	10 ns + (1.00 ns/pF)C <sub>L</sub>	-	60	120	ns
			10 V	9 ns + (0.42 ns/pF)C <sub>L</sub>	-	30	60	ns
			15 V	6 ns + (0.28 ns/pF)C <sub>L</sub>	-	20	40	ns
t <sub>TLH</sub>	LOW to HIGH output transition time	nA or nB to HIGH	5 V	10 ns + (1.00 ns/pF)C <sub>L</sub>	-	60	120	ns
			10 V	9 ns + (0.42 ns/pF)C <sub>L</sub>	-	30	60	ns
			15 V	6 ns + (0.28 ns/pF)C <sub>L</sub>	-	20	40	ns

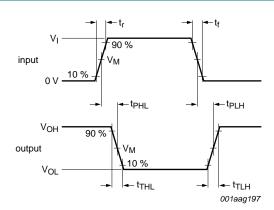
<sup>[1]</sup> Typical value of the propagation delay and output transition time can be calculated with the extrapolation formula (C<sub>L</sub> in pF).

Table 8. Dynamic power dissipation

 $V_{SS} = 0 \ V; \ t_f = t_f \le 20 \ ns; \ T_{amb} = 25 \ ^{\circ}C.$ 

Symbol	Parameter	$V_{DD}$	Typical formula	where:
$P_D$	dynamic power	5 V	$P_D = 2300 \times f_i + \Sigma (f_o \times C_L) \times V_{DD}^2 (\mu W)$	$f_i$ = input frequency in MHz;
	dissipation	10 V	$P_D = 9000 \times f_i + \Sigma (f_o \times C_L) \times V_{DD}^2 (\mu W)$	f <sub>o</sub> = output frequency in MHz;
		15 V	$P_D = 20000 \times f_i + \Sigma (f_o \times C_L) \times V_{DD}^2 (\mu W)$	C <sub>L</sub> = output load capacitance in pF;
				$\Sigma(f_o \times C_L)$ = sum of the outputs;
				$V_{DD}$ = supply voltage in V.

#### 12. Waveforms



Measurement points are given in Table 9.

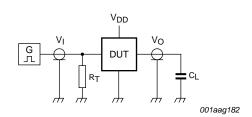
Logic levels:  $V_{OL}$  and  $V_{OH}$  are typical output voltage levels that occur with the output load.

 $t_{\rm r}$ ,  $t_{\rm f}$  = input rise and fall times.

Fig 4. Propagation delay and output transition time

Table 9. Measurement points

Supply voltage	Input	Output
$V_{DD}$	V <sub>M</sub>	V <sub>M</sub>
5 V to 15 V	0.5V <sub>DD</sub>	0.5V <sub>DD</sub>



Test data given in Table 10.

Definitions for test circuit:

DUT = Device Under Test.

 $C_L$  = load capacitance including jig and probe capacitance.

 $R_T$  = termination resistance should be equal to the output impedance  $Z_0$  of the pulse generator.

Fig 5. Test circuit

Table 10. Test data

Supply voltage	Input	Load	
$V_{DD}$	V <sub>I</sub>	t <sub>r</sub> , t <sub>f</sub>	C <sub>L</sub>
5 V to 15 V	V <sub>SS</sub> or V <sub>DD</sub>	≤ 20 ns	50 pF

## 13. Transfer characteristics

Table 11. Transfer characteristics

 $V_{SS} = 0$  V; see Figure 6 and Figure 7.

Symbol	Parameter	Conditions V <sub>DD</sub>	$T_{amb} = -40$ °C to +85 °C			T <sub>amb</sub> = -40 °C to +125 °C		Unit	
				Min	Typ[1]	Max	Min	Max	
$V_{T+}$	positive-going threshold voltage	5 V		2.0	3.0	3.5	2.0	3.5	V
		10 V		3.7	5.8	7.0	3.7	7.0	V
		15 V		4.9	8.3	11.0	4.9	11.0	V
$V_{T-}$	negative-going threshold voltage	5 V		1.5	2.2	3.0	1.5	3.0	V
		10 V		3.0	4.5	6.3	3.0	6.3	V
		15 V		4.0	6.5	10.1	4.0	10.1	V
V <sub>H</sub> I	hysteresis voltage	5 V		0.5	0.8	-	0.5	-	V
		10 V		0.7	1.3	-	0.7	-	V
		15 V		0.9	1.8	-	0.9	-	V

[1] All typical values are at  $T_{amb} = 25 \,^{\circ}C$ .

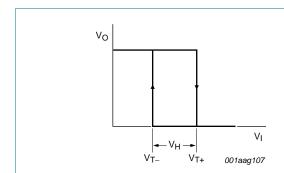


Fig 6. Transfer characteristic

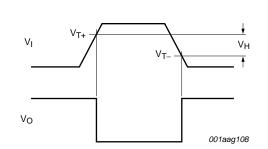
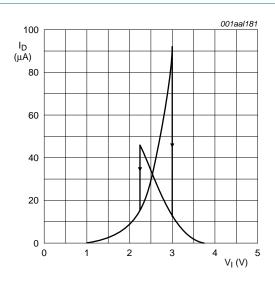
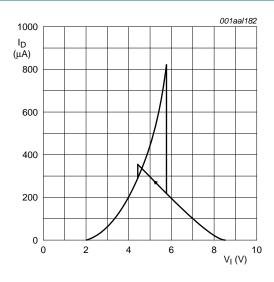
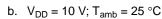


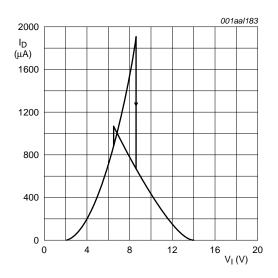
Fig 7. Waveforms showing definition of  $V_{T+}$  and  $V_{T-}$  (between limits at 30 % and 70 %) and  $V_{H}$ 





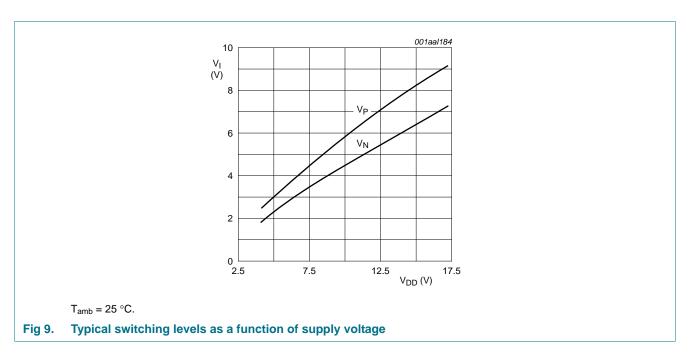
a.  $V_{DD} = 5 \text{ V}$ ;  $T_{amb} = 25 ^{\circ}\text{C}$ 





c.  $V_{DD} = 15 \text{ V}$ ;  $T_{amb} = 25 \,^{\circ}\text{C}$ 

Fig 8. Typical drain current as a function of input



# 14. Application information

Some examples of applications for the HEF40106B-Q100 are:

- · Wave and pulse shapers
- Astable multivibrators
- Monostable multivibrators



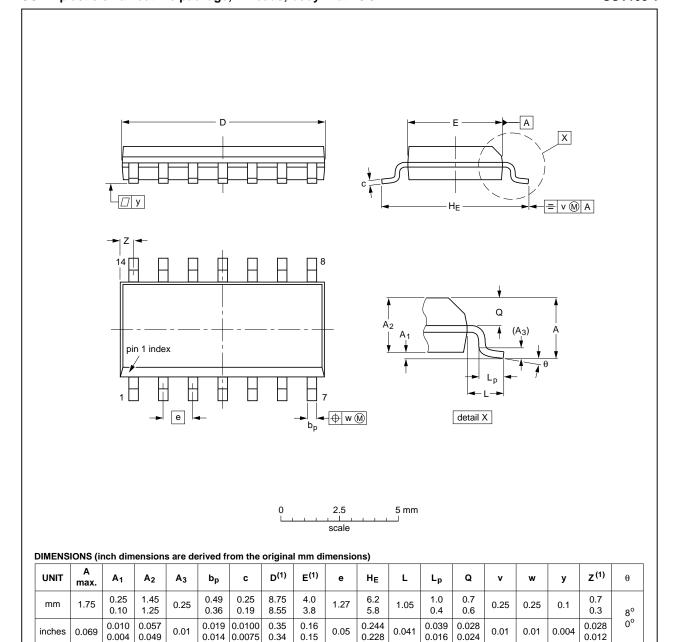
If a Schmitt trigger is driven via a high-impedance (R > 1 k $\Omega$ ), then it is necessary to incorporate a capacitor C with a value of  $\frac{C}{C_P} > \frac{V_{DD} - V_{SS}}{V_H}$ ; otherwise oscillation can occur on the edges of a pulse.

 $C_{\text{p}}$  is the external parasitic capacitance between inputs and output; the value depends on the circuit board layout.

## 15. Package outline

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



#### Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT108-1	076E06	MS-012				<del>99-12-27</del> 03-02-19	

Fig 12. Package outline SOT108-1 (SO14)

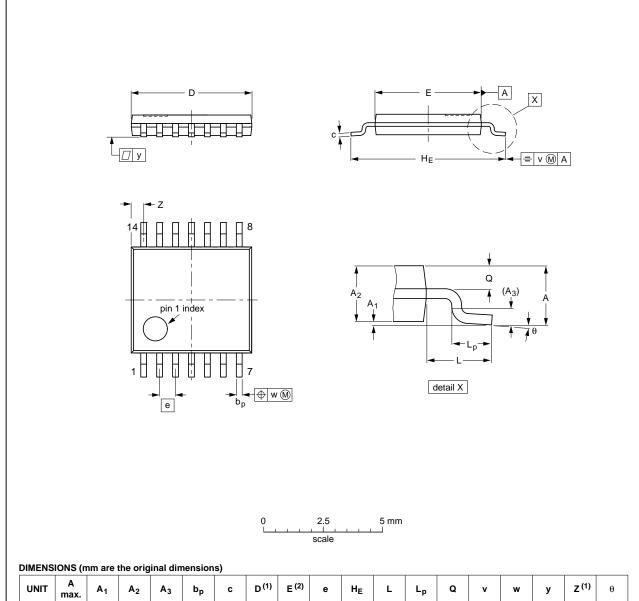
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TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	bp	С	D <sup>(1)</sup>	E (2)	е	HE	L	Lp	Q	v	w	у	Z <sup>(1)</sup>	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT402-1		MO-153				<del>99-12-27</del> 03-02-18	
					1	03-02-16	

Fig 13. Package outline SOT402-1 (TSSOP14)

HEF40106B\_Q100

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## 16. Abbreviations

#### Table 12. Abbreviations

Acronym	Description
НВМ	Human Body Model
ESD	ElectroStatic Discharge
MM	Machine Model
MIL	Military

# 17. Revision history

#### Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
HEF40106B_Q100 v.1	20120807	Product data sheet	-	-

#### 18. Legal information

#### 18.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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# HEF40106B-Q100

#### Hex inverting Schmitt trigger

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## 20. Contents

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